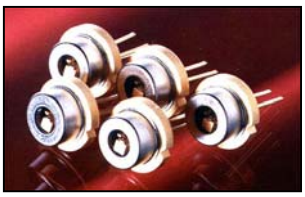
ROITHNER LASERTECHNIK

SCHOENBRUNNER STRASSE 7, VIENNA, AUSTRIA
TEL: +43 -1- 586 52 43-0 FAX: +43 -1- 586 52 43-44
office@roithner-laser.com www.roithner-laser.com

RLT1060-100G TECHNICAL DATA



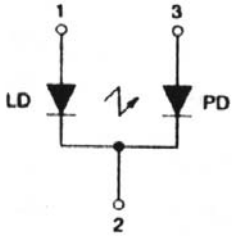
High Power Infrared Laser Diode

Lasing mode structure: **single mode**
Lasing wavelength: **typ. 1060 nm**
Optical power: **100 mW**
Package: **9 mm (SOT-148)**

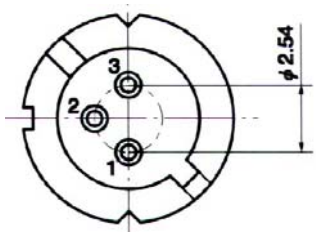
NOTE!
LASERDIODE
MUST BE COOLED!

ATTENTION
OBSERVE PRECAUTIONS
FOR HANDLING
ELECTROSTATIC SENSITIVE DEVICE

PIN CONNECTION:



1) Laser diode anode
2) Laser diode cathode and photodiode cathode
3) Photodiode anode



Absolute Maximum Ratings (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	150	mW
LD Reverse Voltage	$V_{R(LD)}$	1.5	V
PD Reverse Voltage	$V_{R(PD)}$	10	V
Operating Temperature	T_C	-20 .. +40	°C
Storage Temperature	T_{STG}	-40 .. +70	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Emitting Aperture	A	cw		1 x 5		µm²
Optical Output Power	P_o	single mode		100		mW
Threshold Current	I_{th}	cw	20	25	30	mA
Operation Current	I_{op}	P_o = 100 mW	120	130	140	mA
Forward Voltage	U_f	P_o = 100 mW	1.2	1.3	1.4	V
Lasing Wavelength	λ_p	P_o = 100 mW	1054	1060	1064	nm
Spectral Width FWHM	$\Delta\lambda$	P_o = 100 mW		0.2	0.3	nm
Beam Divergence	$\theta_{//}$	P_o = 100 mW		25		°
Beam Divergence	$\theta_{\perp}$	P_o = 100 mW		40		°
Monitor Current	I_m	P_o = 100 mW	100	500	1500	µA